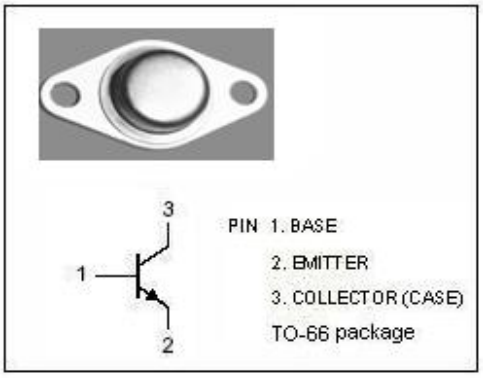
isc Silicon NPN Power Transistor 2N5661



DESCRIPTION

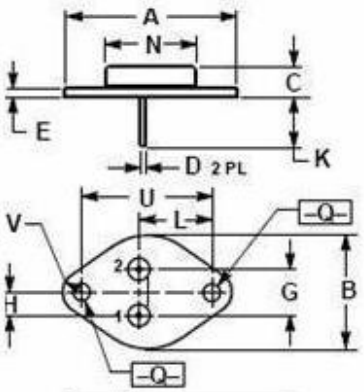
- Collector-Emitter Breakdown Voltage-
  : V_{CEO}=300V(Min)
- Minimum Lot-to-Lot variations for robust device Performance and reliable operation

APPLICATIONS

- Power amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	400	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	2	A
P_D	Collector Power Dissipation @ T_C=25℃	2	W
T_J	Junction Temperature	-65~200	℃
T_{stg}	Storage Temperature Range	-65~200	℃



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.90
C	6.70	7.10
D	0.70	0.90
E	1.40	1.80
G	5.08	
H	2.54	
K	9.80	10.50
L	14.70	14.90
N	12.40	12.70
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C=10mA	300			V
I_{CBO}	Collector-Base Cutoff Current	V_{CB}= 300V			0.1	uA
I_{CEO}	Collector-Emitter Cutoff Current	V_{CE}= 300V			0.2	uA
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 1A; I_B= 0.1A			0.4	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 2A; I_B= 0.4A			0.8	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C= 1A; I_B= 0.1A			1.2	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	I_C= 2A; I_B= 0.4A			1.5	V
h_{FE-1}	DC Current Gain	I_C=50mA; V_{CE}= 2V	25			
h_{FE-2}	DC Current Gain	I_C=500mA; V_{CE}= 5V	25		75	
h_{FE-3}	DC Current Gain	I_C=1A; V_{CE}= 5V	15			
h_{FE-4}	DC Current Gain	I_C=2A; V_{CE}= 5V	5			